An Experimental Evaluation of X-Band GaAs FET Mixers Using Single and Dual-Gate Devices

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Experimental results are presented for X-band GaAs FET mixers. Two circuits using commercially available single-gate devices have yielded good conversion gains at 10 GHz, and a specially developed dual-gate device in a simple microwave circuit has yielded 11 dB conversion gain and 6.5 dB noise figure (D.S.B.), at 10 GHz.

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